

L Number	Hits	Search Text	DB	Time stamp
-	253	(silicon adj (dioxide or oxide)) same epitax\$4 and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/26 15:34
-	113	(silicon adj (dioxide or oxide)) same epitax\$4 and 117/\$4.ccls. and cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/26 15:36
-	66	(silicon adj (dioxide or oxide)) near20 epitax\$4 and 117/\$4.ccls. and cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/16 15:36
-	375	(silicon adj (dioxide or oxide)) near40 crystal\$5 and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/26 15:51
-	140	(silicon adj (dioxide or oxide)) near40 crystal\$5 and 117/\$4.ccls. and cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/26 17:30
-	2	ethyl\$1silicate and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/26 17:37
-	6	quartz near2 (layer or film) and buffer near2 (gan or zno or gallium adj nitride or zinc adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/16 14:54
-	70	quartz near2 (layer or film) same (gan or zno or gallium adj nitride or zinc adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/16 15:19
-	87	quartz near2 (layer or film) same buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/17 11:03
-	2	quartz near2 buffer and (zno or zinc adj oxide or gan or gallium adj nitride) near10 buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/16 15:34
-	88	(silicon adj (dioxide or oxide)) near20 epitax\$4 and 117/\$4.ccls. and cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/16 15:45